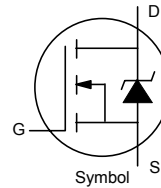
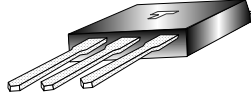




IRF840LCS/LCL

Power MOSFET

$V_{DS} = 500V$, $R_{DS(on)} = 0.85 \text{ ohm}$, $I_D = 8.0 A$



N Channel

ELECTRICAL CHARACTERISTICS at $T_J = 25^\circ\text{C}$ Maximum. Unless stated Otherwise						
Parameter	Symbol	Test Conditions	Value			Unit
			Min	Typ	Max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 V_{DC}$, $I_D = 250\mu A$	500	-	-	Volt
Drain to Source Leakage Current	I_{DSS}	$V_{DS} = 500V_{DC}$, $V_{GS} = 0V_{DC}$	-	-	25	μA
		$V_{DS} = 400V_{DC}$, $V_{GS} = 0V_{DC}$, $T_J = 125^\circ\text{C}$	-	-	250	
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = +20V_{DC}$	-	-	100	nA
		$V_{GS} = -20V_{DC}$	-	-	-100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2.0	-	4.0	Volt
Static Drain to Source On - Resistance	$R_{DS(on)}$	$V_{GS} = 10V_{DC}$, $I_D = 4.8A$	-	-	0.85	Ω
Gate Charge	Q_G	$I_D = 8.0A$	-	-	39	nC
Gate to Source Charge	Q_{GS}	$V_{DS} = 400V_{DC}$, $V_{GS} = 10V_{DC}$	-	-	10	nC
Gate to Drain Charge	Q_{GD}		-	-	19	nC
Input Capacitance	C_{iss}	$V_{DS} = 25V_{DC}$, $V_{GS} = 0V_{DC}$, $f = 1.0\text{MHz}$	-	1100	-	pF
Output Capacitance	C_{oss}		-	170	-	pF
Transfer Capacitance	C_{rss}		-	18	-	pF
Turn On Delay Time	$t_{d(on)}$	$V_{DD} = 250V_{DC}$, $I_D = 8.0A$, $R_G = 9.1\Omega$ $R_D = 31\Omega$	-	12	-	nS
Turn Off Delay Time	$t_{d(off)}$		-	27	-	nS
Rise Time	t_r		-	25	-	nS
Fall Time	t_f		-	19	-	nS
Continuous Source Current	I_S		-	-	8.0	A
Pulsed Source Current	I_{SM}		-	-	28	A
Forward Voltage (Diode)	V_{SD}	$V_{GS} = 0V_{DC}$, $I_S = 8.0A$, $T_p = 300\mu S$	-	-	2.0	V
Single Pulse Avalanche Energy	E_{AS}				510	mJ

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless stated otherwise)				
Parameter	Symbol	Condition	Value	Unit
Gate to Source Voltage	V_{GS}		$\pm 30V$	Volt
Drain to Source Voltage	V_{DS}		500	Volt
Continuous Drain Current	I_D		8.0	Amp
Pulsed Drain Current	I_{DM}	-	28	Amp
Total Power Dissipation	P_D	($T_A = 25^\circ\text{C}$)	125	W
Thermal Resistance (Junction to Ambient)	$R_{TH} (\mu A)$		40	$^\circ\text{C/W}$

Maximum Operating Temperature Range (T_J) -55 to $+150^\circ\text{C}$
Maximum Storage Temperature Range (T_{stg}) -55 to $+150^\circ\text{C}$



IRF840AS/AL

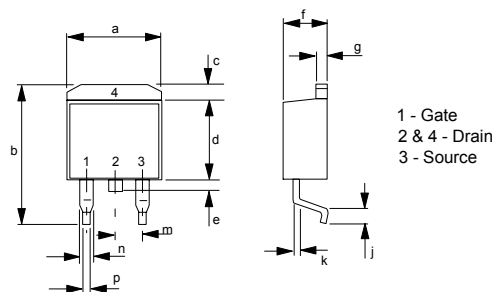
Power MOSFET

$V_{DS} = 500V$, $R_{DS(on)} = 0.85 \text{ ohm}$, $I_D = 8.0 A$

Mechanical Dimensions

Case SMB 220 Plastic

Dim	Millimetres		Inches	
	Min	Max	Min	Max
a	9.85	10.67	0.380	0.420
b	14.61	15.88	0.575	0.625
c		1.65		0.065
d	8.51	9.65	0.335	0.380
e	1.27	1.78	0.050	0.070
f	4.08	4.83	0.160	0.190
g	1.14	1.40	0.045	0.055
h	1.15	1.400	0.045	0.055
j	1.78	2.79	0.070	0.110
k	0.38	0.77	0.015	0.029
m		2.54 Pitch		0.10 Pitch
n	0.51	0.99	0.020	0.038
p	0.51	0.89	0.020	0.35



Mechanical Dimensions

Case TO262 Plastic

Dim	Millimetres		Inches	
	Min	Max	Min	Max
a	10.29	10.54	0.405	0.415
b	9.91	10.54	0.390	0.415
c	13.47	14.09	0.530	0.555
d	1.15		0.045	
e	1.15	1.40	0.045	0.055
f	0.69	0.93	0.027	0.037
g		2.54 Pitch		0.10 Pitch
h	4.20	4.69	0.165	0.185
j	1.22	1.32	0.048	0.052
k	0.46	0.55	0.018	0.022
m	2.64	2.92	0.104	0.115
n	3.55	4.06	0.140	0.160

